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2017 International Workshop on EUV Lithography

(2017 EUVL Workshop)

CXRO, LBNL, Berkeley, CA, USA June 12-15, 2017

Workshop Proceedings

Wednesday, June 14, 2017

8:00 AM Welcome and Introduction

Welcome to LBL (Historical Perspective on EUVL) (PO)4 Glen Kubiak, LBL

Welcome to 2017 EUVL Workshop Vivek Bakshi EUV Litho, Inc., Austin, TX, USA

Introductions and Announcements (Intro-1)N/A Patrick Naulleau, LBL

Session 1: Keynote – 1

Session Chair: Anthony Yen (ASML)

EUVL: Current Status & Remaining Challenges (P1) (Keynote Presentation)6 Obert R Wood II GLOBALFOUNDRIES,400 Stone Break Road Extension, Malta, New York 12020, U.S.A.

EUV Lithography for HVM (P3) (Keynote Presentation)9 Britt Turkot Intel Corporation

Break (20 minutes)

Session 2: EUV Masks and Mask Metrology

Session Co-chairs: Jim Wiley (ASML) and Bryan Kasprowicz (Photronics)

EUV Mask Economics: Impact of Mask Costs on Patterning Strategy (P33)27 (Invited Paper)

Bryan S. Kasprowicz¹ and Michael Lercel² ¹Photronics, Inc. ²ASML, Inc.

Reduction of Large Killer Defects in EUV Mask Blanks (P39) (Invited Paper)33

Adrian Devasahayam, Alan V. Hayes, Boris Druz, <u>Sandeep Kohli</u>, Rustam Yevtukhov, *Veeco Instruments Inc (United States)*

NewSUBARU EUVL R&D Activities and EUV Mask Defect Inspection (P34)

(Invited Paper)28

<u>Takeo Watanabe</u> and Tetsuo Harada Center for EUVL, Laboratory of Advanced Science and Technology for Industry, University of Hyogo

Anamorphic Imaging: Emulating Future Nodes of EUV Lithography on the SHARP Microscope (P38)32

<u>Markus Benk</u>, Weilun Chao, Ryan Miyakawa, Kenneth Goldberg, Patrick Naulleau Lawrence Berkeley National Laboratory, Center for X-ray Optics, 1 Cyclotron Road, Berkeley, California, United States, 94720

Characterization of SiN-based membrane for EUV pellicle application (P60)N/A Jinho Ahn

Division of Materials Science and Engineering Hanyang University, 222 Wangsimni-ro, Seongdong-gu, Seoul 04763, Republic of Korea

RESCAN - A Standalone Tool for EUV Mask Defect Inspection (P32)26

Patrick Helfenstein^a, Iacopo Mochi^a, Rajeev Rajendran^a, Istvan Mohacsi^a, Yoshitake Shusuke^b, Yasin Ekinci^a ^aPaul Scherrer Institute, Villigen PSI, Villigen, CH-5232, Switzerland ^bNuFlare Technology, Inc., 8-1 Shinsugita-cho, Yokohama 235-8522, Japan

<u>Rigorous 3D Electromagnetic Simulation of Ultrahigh Efficiency EUV Contact-hole</u> <u>Printing with Chromeless Phase-shift Mask (P37)</u>31

Stuart Sherwin^a, Thomas V. Pistor, Andrew Neureuther^a, and Patrick Naulleau^b ^aUniversity of California, Berkeley, Department of Electrical Engineering and Computer Sciences, Berkeley, California, United States, 94720 ^bLawrence Berkeley National Laboratory, Center for X-ray Optics, 1 Cyclotron Road, Berkeley, California, United States, 94720

Lunch 12:20 AM – 1:20 PM

Session 3: EUV Sources- I

Session Co-chairs: Akira Endo (HiLASE) and Oscar Versolato (ARCNL)

<u>kW-class Picosecond Thin-disk Pre-pulse Laser PERLA for Efficient EUV</u> <u>Generation (P11) (Invited Paper)</u>12

<u>Akira Endo¹</u>, Martin Smrž¹, Jiří Mužík^{1,2}, Ondřej Novák¹, Michal Chyla¹, Tomáš Mocek¹

¹ HiLASE Centre, Institute of Physics AS CR, Za Radnicí 828, 252 41 Dolní Břežany, Czech Republic

² Faculty of Nuclear Sciences and Physical Engineering, Czech Technical University in Prague, Břehová 7, 115 19 Praha 1, Czech Republic

Scalability of CO₂ Amplifiers to Generate Stable > 500W Extreme Ultraviolet (EUV) Beams (P12) (Invited Paper)13

Koji Yasui¹, Naoyuki Nakamura², Jun-ichi Nishimae²,

Masashi Naruse³, Kazuo Sugihara³, and Masato Matsubara³

¹*Mitsubishi Electric Corporation, Head quarter, Factory Automation Systems Group, Tokyo, Japan*

²*Mitsubishi Electric Corporation, Advanced technology R&D center, Hyogo, Japan* ³*Mitsubishi Electric Corporation, Nagoya works, Nagoya, Japan*

Simulating EUV Production – an Overview of the Underpinnings (P13) (Invited Paper)14

Howard Scott and Steve Langer Lawrence Livermore National Laboratory, USA

Short-pulsed Nd:YAG Laser Interaction with Tin Micro-droplets (P14) (Invited Paper)15

Oscar O. Versolato Advanced Research Center for Nanolithography (ARCNL), Science Park 110, 1098 XG Amsterdam, The Netherlands

Break and Group Photograph 2:20 PM (30 Minutes)

Session 4: EUV Sources - II

Session Chair: Erik R. Hosler (GLOBALFOUNDRIES) and Hiroshi Kawata (KEK)

Next Generation Source Power Requirements: What will we need at the 3 nm node and beyond? (P15) (Invited Paper)16 Erik R. Hosler GLOBALFOUNDRIES, 400 Stone Break Road Extension, Malta, NY 12020

A Compact Linac-Driven EUV Light Source utilizing a Short-Period Microwave-Driven Undulator (P16)17

<u>Filippos Toufexis</u>*, Cecile Limborg-Deprey, Valery A. Dolgashev, Sami G. Tantawi SLAC National Accelerator Laboratory, 2575 Sand Hill Rd, Menlo Park, California 94025 * Also at the Department of Electrical Engineering, Stanford University

Concept for 1kW EUV Source for Lithography Based on FEL Emission in Compact Storage Ring (P17) (Invited Paper)18

Michael Feser Lyncean Technologies Inc.

<u>Challenges to Realize the EUV-FEL High Power Light Source - Present Status on</u> <u>the EUV-FEL R&D Activities (P18) (Invited Paper)</u>19

Hiroshi Kawata High Energy Accelerator Research Organization (KEK), Tsukuba, Ibaraki 305-0801, Japan

Session 5: Poster Session 5:30 7:00 PM

Session Chair: Gregory Denbeaux (SUNPU Poly)

Large Collector Mirror Reflectometer for the High Power EUV Light Source Achievement (P25)24

Takeo Watanabe and Tetsuo Harada

Center for EUVL, Laboratory of Advanced Science and Technology for Industry, University of Hyogo

Measuring Aberrations with Mask Roughness (P35)29

Aamod Shanker Dept. of Electrical Engineering and Computer Sciences, University of California, Berkeley, CA

Impact of Tool Design on Defect Detection Sensitivity for EUV Actinic Blank Inspection (P36)**30**

Yow-Gwo Wang,^{a,b,*} Andrew R. Neureuther,^{a,b} Patrick P. Naulleau^b ^aUniversity of California, Berkeley, Department of Electrical Engineering and Computer Sciences, Berkeley, California, United States, 94720 ^bLawrence Berkeley National Laboratory, Center for X-ray Optics, 1 Cyclotron Road, Berkeley, California, United States, 94720

Variable Separation Method for Three-dimensional EUVL Mask Diffraction Simulation (P40)34

<u>Xiangzhao Wang</u>*, Heng Zhang, Sikun Li Laboratory of Information Optics and Opto-electronic Technology, Shanghai Institute of Optics and Fine Mechanics, Chinese Academy of Sciences, Shanghai, China, 201800</u>

Improved Inspection Ability of Coherent Scattering Microscopy by Applying Ptychography (P31)25

Winner of First Place in the Poster Session

Young Woong Kim¹, Dong Gon Woo¹, Seung Hyuk Shin², Hoon Jo², Whoi-Yul Kim² and Jinho Ahn¹

¹Division of Materials Science and Engineering

²Department of Electronics and Computer Engineering

Hanyang University, 222 Wangsimni-ro, Seongdong-gu, Seoul 04763, Republic of Korea

<u>Coherent diffraction imaging with partially coherent discharge plasma based EUV</u> <u>sources (P61)</u>45

Jan Bußmann^{1,2}, Michal Odstrcil^{1,3}, Raoul Bresenitz¹, Yusuke Teramoto⁴, Marco Perske⁵, Torsten Feigl⁵, William S. Brocklesby³, Larissa Juschkin^{1,2}

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² Peter Grünberg Institute 9, JARA-FIT, Forschungszentrum Jülich GmbH, 52425 Jülich, Germany

³ Optoelectronics Research Center, University of Southampton, SO17 1BJ, United Kingdom

⁴ BLV Licht- und Vakuumtechnik GmbH, Steinbachstraße 15, Aachen, Germany

⁵ OptiXfab. GmbH, Hans-Knoell-Str. 6, 07745 Jena, Germany

Achromatic Talbot lithography with partially coherent EUV radiation (P62)46

Sascha Brose¹, Jenny Tempeler¹, Hyun-su Kim^{2,3}, Serhiy Danylyuk¹, Peter Loosen¹, Larissa Juschkin^{2,3}

¹ Chair for the Technology of Optical Systems, JARA-FIT, RWTH Aachen University, Germany

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<u>Spectroscopic EUV reflectometry for characterization of thin films and layered</u> <u>structures (P63)</u>47

Maksym Tryus¹, Serhiy Danylyuk², Daniel Wilson³, Stefan Herbert², Lukas Bahrenberg², Angelo Giglia⁴, Piergiorgio Nicolosi⁵, and Larissa Juschkin^{1,3}

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⁵ Dipartimento di Ingegneria dell'Informazione, Universita' degli Studi di Padova, Italy

EUV scattering metrology: Benchmarking of discharge plasma source based table-top scatterometry versus PTB synchrotron based EUV radiometry (P64)**48** Oleksiy Maryasov^{1,2}, Christian Laubis², Mewael Sertsu^{1,3}, Frank Scholze²,

Larissa Juschkin^{1,4}

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⁴ Peter Grünberg Institute 9, Forschungszentrum Jülich GmbH, 52425 Jülich, Germany

Estimation of Lithographically-relevant Secondary Electron Blur (P51)43 Winner of Second Place in the Poster Session

<u>Roberto Fallica</u> and Yasin Ekinci Paul Scherrer Institute, 5232 Villigen PSI, Switzerland

EUV Lithography Research and Development Activities at University of Hyogo (P52)44

<u>Takeo Watanabe</u> and Tetsuo Harada Center for EUVL, Laboratory of Advanced Science and Technology for Industry, University of Hyogo

EUV Light Source Development at Energetiq (P65) (Commercial Poster)N/A Matthew Partlow, Energetiq

Laser Driven Light Sources (LDLS) from Energetiq (P66) (Commercial Poster)N/A Matthew Partlow, Energetiq

Veeco's Technologies Enable High Growth Markets (P67) (Commercial Poster).....N/A Sandeep Kohli, Veeco

End Day 1

Thursday, June 15, 2017

Welcome and Announcements (Intro-2)

Patrick Naulleau, LBL

Session 6: Keynote-2

Session Chair: Patrick Naulleau (LBL)

 Tabletop Coherent EUV Sources and Applications: Full Field Sub-Wavelength

 Imaging at 13.5nm and Materials Metrology (P4) (Keynote Presentation)

 Margaret Murnane

 JILA, University of Colorado at Boulder and KMLabs Inc.

High Power HVM LPP-EUV Source with Long Collector Mirror Lifetime (P2) (Keynote Presentation)7 Hakaru Mizoguchi Gigaphoton Inc., Hiratsuka Kanagawa,254-8567, JAPAN

EUV Lithography: Progress in LPP Source Power Scaling and Availability (P5) (Keynote Presentation)11

Igor Fomenkov Cymer LLC, An ASML Company, San Diego, CA 92127, USA

Break (20 Minutes)

Session 7: Optics and Contamination

Session Co-Chairs: Jan van Schoot (ASML) and Ladislav Pina (RITE

EUV Optics Life-time Research: Past, Present and Future (P21) (Invited Review paper)20

<u>Norbert Koster</u>, Edwin te Sligte, Arnold Storm, Herman Bekman, Jacques van der Donck, Diederik Maas, Jochem Janssen, Rogier Verberk *TNO, Stieltjesweg 1, 2628 CK Delft, The Netherlands*

The Future of EUV Lithography: Enabling Moore's Law in the Next Decade (P22) (Invited Paper)21

Jan van Schoot, Kars Troost, Alberto Pirati, Rob van Ballegoij, Peter Krabbendam, Judon Stoeldraijer, Erik Loopstra, Jos Benschop, Jo Finders, Hans Meiling, Eelco van Setten, Bernhard Kneer*, Bernd Thuering*, Winfried Kaiser*, Tilmann Heil*, Sascha Migura* ASML Netherlands B.V., De Run 6501, 5504 DR Veldhoven, The Netherlands *Carl Zeiss SMT GmbH, Rudolf-Eber-Straße 2, 73447 Oberkochen

Latest Developments in EUV Optics (P23) (Invited Paper)22

<u>Jack Liddle</u>, Joerg Zimmermann, Jens Timo Neumann, Matthias Roesch, Ralf Gehrke, Bernhard Kneer, *Eelco van Setten, *Jan van Schoot *Carl Zeiss SMT GmbH, Rudolf-Eber-Straße 2, 73447 Oberkochen* *ASML Netherlands B.V., De Run 6501, 5504 DR Veldhoven, The Netherlands

EUV/SXR Optics and Metrology Development at RITE (P24) (Invited Paper)23

Ladislav Pina Rigaku Innovative Technologies Europe (RITE), Prague, Czech Republic

Lunch 12:00 PM (60 Minutes)

Steering Committee working lunch meeting (Closed meeting)

Session 8: Resist and Patterning -1

Session Co-Chairs: Greg McIntyre (IMEC) and Yoshi Hishiro (JSR)

EUVL Developments at Imec (P47) (Invited Paper)**40** Greg McIntyre *IMEC*

<u>Reactivity of Metal Oxalate EUV Resists as a Function of the Central Metal (P41)</u> (Invited Paper)35

Steven Grzeskowiak,^a Amrit Narasimhan,^a Michael Murphy,^a Lee Napolitano,^b Daniel A. Freedman,^b Robert L. Brainard,^a and <u>Greg Denbeaux</u>^a ^a State University of New York Polytechnic Institute - CNSE, 257 Fuller Rd. Albany, NY 12203

^b State University of New York at New Paltz, 1 Hawk Drive New Paltz, NY 12561

Novel EUV resist development for sub-7 nm node (P43) (Invited Paper)37

Yoshi Hishiro JSR Micro INC, 1280 N. Mathilda Ave, Sunnyvale, CA 94089, USA

Metal Oxide Photoresists: Breaking Paradigms in EUV Lithography (P50) (Invited

Paper)42 Jason Stowers Inpria

Fundamental Aspect of Photosensitized Chemically Amplified Resist: How to overcome RLS trade-off (P46) (Invited Paper)N/A

Seiichi Tagawa^{1,2}

¹Graduate School of Engineering, Osaka University, Ibaraki, Osaka 567-0047, Japan, ²Institute of Scientific and Industrial Research, Osaka University, Ibaraki, Osaka 567-0047, Japan

Break 2:50 PM (20 Minutes)

Session 9: Resist and Patterning -2

Session Co-chairs: Greg Denbeaux (SUNY Poly) and Frank Ogletree (LBL)

Towards Real-Time Analysis of Morphologies using Scattering (P42) (Invited Paper)36

Alex Hexemer

Lawrence Berkeley National Laboratory, Berkeley, California, United States, 94720

Extreme ultraviolet Induced Chemical Reactions in Photoresists and Model Systems (P44) (Invited Paper)38

<u>S. Castellanos</u>^a, Y. Zhang^a, J. Haitjema^a, L. Wu^a, O. Luigier^a, D. Kazazis^b, M. Vockenhuber^b, T. R. Fallica^b, Y. Ekinci^b, A.M. Brouwer^a.

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^b Paul Scherrer Institute, 5232 Villigen PSI, Switzerland

Fundamentals of X-Ray Excitation and Relaxation in EUV Resists (P45) (Invited Paper)N/A

D. Frank Ogletree Molecular Foundry, Materials Sciences Division, Lawrence Berkeley National Laboratory, 1 Cyclotron Road, Berkeley CA 94720 USA

Fundamental Aspects of Low Energy Electron Driven Chemistry (P48) (Invited

Paper)41 Dan Slaughter Chemical Sciences Division, LBNL

EUVL Workshop Summary (P70)N/A

Vivek Bakshi EUV Litho, Inc.

Depart for Dinner

6:00 -9:00 PM Dinner Cruise